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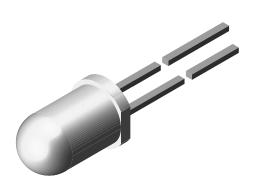
### **TSFF6210**

HALOGEN

FREE GREEN

## Vishay Semiconductors

# High Speed Infrared Emitting Diode, 870 nm, GaAlAs Double Hetero



### **DESCRIPTION**

TSFF6210 is an infrared, 870 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### **FEATURES**

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

Peak wavelength: λ<sub>p</sub> = 870 nm

· High reliability

· High radiant power

· High radiant intensity

• Angle of half intensity:  $\varphi = \pm 10^{\circ}$ 

· Low forward voltage

· Suitable for high pulse current operation

• High modulation bandwidth: f<sub>c</sub> = 24 MHz

· Good spectral matching with Si photodetectors

 Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

### **APPLICATIONS**

- Infrared video data transmission between Camcorder and TV set
- Free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- · Smoke-automatic fire detectors

PRODUCT SUMMARY					
COMPONENT	I <sub>e</sub> (mW/sr)	φ (°)	$\lambda_{\mathbf{p}}$ (nm)	t <sub>r</sub> (ns)	
TSFF6210	180	± 10	870	15	

#### Note

· Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSFF6210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

#### Note

• MOQ: minimum order quantity

# **TSFF6210**

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ABSOLUTE MAXIMUM RATINGS (T <sub>amb</sub> = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V <sub>R</sub>	5	V	
Forward current		I <sub>F</sub>	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I <sub>FM</sub>	200	mA	
Surge forward current	t <sub>p</sub> = 100 μs	I <sub>FSM</sub>	1	Α	
Power dissipation		P <sub>V</sub>	180	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T <sub>amb</sub>	-40 to +85	°C	
Storage temperature range		T <sub>stg</sub>	-40 to +100	°C	
Soldering temperature	t ≤ 5 s, 2 mm from case	T <sub>sd</sub>	260	°C	
Thermal resistance junction to ambient	J-STD-051, leads 7 mm, soldered on PCB	R <sub>thJA</sub>	230	K/W	

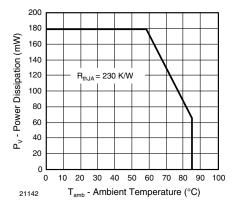


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

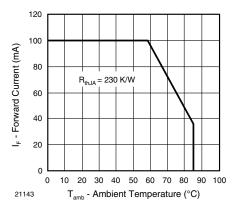


Fig. 2 - Forward Current Limit vs. Ambient Temperature

<b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V <sub>F</sub>	-	1.5	1.8	V
	$I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$	V <sub>F</sub>	-	2.3	3.0	V
Temperature coefficient of V <sub>F</sub>	I <sub>F</sub> = 1 mA	TK <sub>VF</sub>	-	-1.8	-	mV/K
Reverse current	V <sub>R</sub> = 5 V	I <sub>R</sub>	-	-	10	μΑ
Junction capacitance	V <sub>R</sub> = 0 V, f = 1 MHz, E = 0	C <sub>j</sub>	-	125	-	pF
Dadient intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l <sub>e</sub>	90	180	450	mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$	I <sub>e</sub>	-	1800	-	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе	-	50	-	mW
Temperature coefficient of φ <sub>e</sub>	I <sub>F</sub> = 100 mA	TKφ <sub>e</sub>	-	-0.35	-	%/K
Angle of half intensity		φ	-	± 10	-	0
Peak wavelength	I <sub>F</sub> = 100 mA	$\lambda_{p}$	-	870	-	nm
Spectral bandwidth	I <sub>F</sub> = 100 mA	Δλ	-	40	-	nm
Temperature coefficient of $\lambda_p$	I <sub>F</sub> = 100 mA	TKλ <sub>p</sub>	-	0.25	-	nm/K
Rise time	I <sub>F</sub> = 100 mA	t <sub>r</sub>	-	15	-	ns
Fall time	I <sub>F</sub> = 100 mA	t <sub>f</sub>	-	15	-	ns
Cut-off frequency	I <sub>DC</sub> = 70 mA, I <sub>AC</sub> = 30 mA pp	f <sub>c</sub>	-	24	-	MHz
Virtual source diameter		d	-	3.7	-	mm

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### BASIC CHARACTERISTICS (T<sub>amb</sub> = 25 °C, unless otherwise specified)

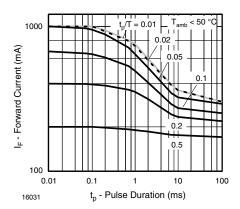


Fig. 3 - Pulse Forward Current vs. Pulse Duration

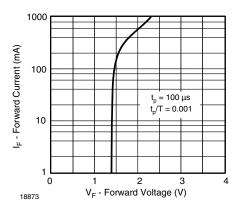


Fig. 4 - Forward Current vs. Forward Voltage

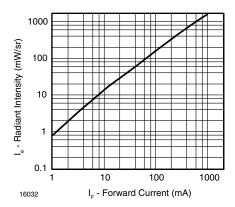


Fig. 5 - Radiant Intensity vs. Forward Current

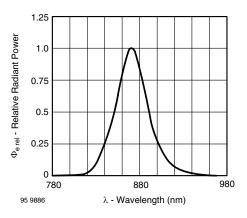


Fig. 6 - Relative Radiant Power vs. Wavelength

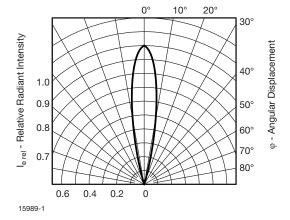


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

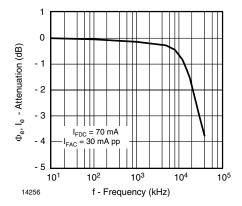
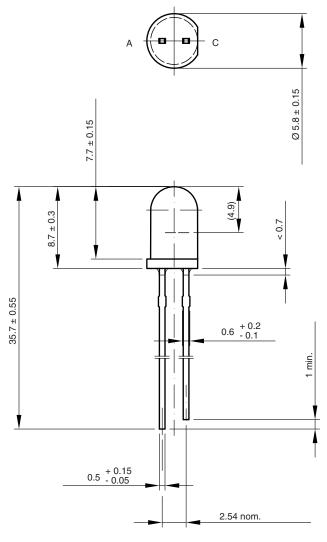


Fig. 8 - Attenuation vs. Frequency

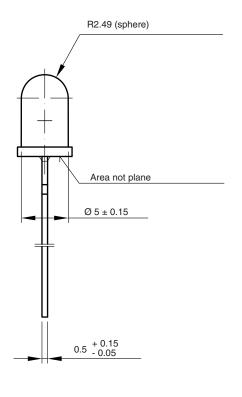
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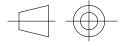
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### **PACKAGE DIMENSIONS** in millimeters



6.544-5259.09-4 Issue: 4; 19.05.09 20161





technical drawings according to DIN specifications



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